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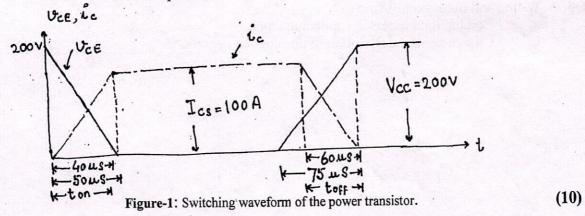
M.E. Electrical Engineering (Power System) Second Semester

EE-8209 (a): Advanced Power Electronics Techniques and Devices for Power Systems

Time allowed: 3 Hours Max. Marks: 50

NOTE: Attempt <u>any five</u> questions. Assume suitably missing data, if any.

Q1. A power transistor has its switching wave-shape as shown in Figure-1. If the average power loss in the transistor is limited to 300 W, find the switching frequency at which this transistor can be operated.



- Q2.a. Explain the static characteristics of *n*-channel Power Metal-oxide-semiconductor Field-effect transistor with the help of its basic circuit diagram. (6)
- b. Clearly indicate the turn-on and turn-off state in static output characteristics of the same.
- c. Also, explain the dynamic turn-on process in its switching characteristics with appropriate wave-form. (3)
- Q3.a. Explain the working of an insulated gate bipolar transistor with help of approximate and exact equivalent circuit representations. (5)
- b. Only write the equation for on-state voltage drop across it. (1)
- c. Explain in detail the dynamic turn-off characteristics of the same. (4)
- Q4. A thyristor operating from a peak supply voltage of 400 V has the following specifications:

Repetitive peak current, $I_p=200$ A, $(dv/dt)_{max}=50$ A/microseconds, $(dv/dt)_{max}=200$ V/microseconds.

Choosing a factor of safety for I_P, (di/dt)_{max}, and (dv/dt)_{max}, design a suitable snubber circuit. The minimum value of load resistance is 10 ohms. (10)

- Q5. Explain the dynamic turn-on and turn-off processes of a Gate Turn-off thyristor with the help of appropriate wave-form representations. (10)
- Q6.a. With the help of suitable waveform representations, clearly explain the reverse recovery characteristics of the power diode.
- b. And hence, derive the term peak inverse current, I_{RM} in terms of stored charge, Q_R for the same. (06, 04)
- Q. 7. Explain safe operating areas of power transistor and insulated gate bipolar transistor.

 (5+5)
- Q8. Write short notes on following:
 - Conduction process in semiconductors.
 - b. Charge control description of pn-junction operation.

(5, 5)